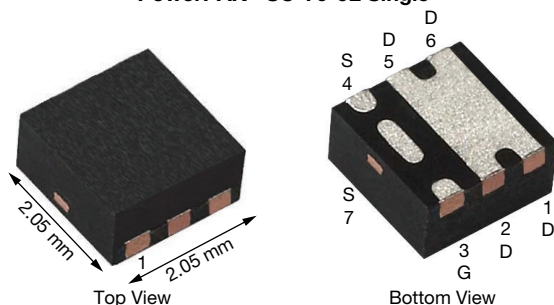


# P-Channel 30 V (D-S) MOSFET

**PowerPAK® SC-70-6L Single**

**Marking code: KD**

## PRODUCT SUMMARY

$V_{DS}$ (V)	-30
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = -10$ V	0.045
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = -4.5$ V	0.053
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = -2.5$ V	0.081
$Q_g$ typ. (nC)	10.6
$I_D$ (A) <sup>a, e</sup>	-9
Configuration	Single

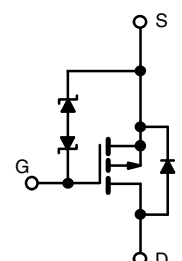
## FEATURES

- TrenchFET® power MOSFET
- 100 %  $R_g$  tested
- Thermally enhanced PowerPAK® SC-70 package
  - Small footprint area
  - Low on-resistance
- Typical ESD protection: 3000 V (HBM)
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

## APPLICATIONS

- Power management for portable and consumer
- Load switch
- Charger switches
- Battery switches



P-Channel MOSFET

## ORDERING INFORMATION

Package	PowerPAK SC-70
Lead (Pb)-free and halogen-free	SiA4371EDJ-T1-GE3

## ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	-30	V
Gate-source voltage	$V_{GS}$	$\pm 12$	
Continuous drain current ( $T_J = 150$ °C)	$I_D$	$T_C = 25$ °C	-9 <sup>e</sup>
		$T_C = 70$ °C	-9 <sup>e</sup>
		$T_A = 25$ °C	-6.4 <sup>b, c</sup>
		$T_A = 70$ °C	-5.1 <sup>b, c</sup>
Pulsed drain current ( $t = 300$ $\mu$ s)	$I_{DM}$	-20	
Continuous source-drain diode current	$I_S$	$T_C = 25$ °C	-9 <sup>e</sup>
		$T_A = 25$ °C	-2.4 <sup>b, c</sup>
Maximum power dissipation	$P_D$	$T_C = 25$ °C	15.6
		$T_C = 70$ °C	10
		$T_A = 25$ °C	2.9 <sup>b, c</sup>
		$T_A = 70$ °C	1.9 <sup>b, c</sup>
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	°C
Soldering recommendations (peak temperature) <sup>c, d</sup>		260	

## THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>b, d</sup>	$R_{thJA}$	32	43	°C/W
Maximum junction-to-case (drain)	$R_{thJC}$	6	8	

### Notes

- $T_C = 25$  °C
- Surface mounted on 1" x 1" FR4 board
- $t = 5$  s
- Maximum under steady state conditions is 80 °C/W
- Package limited



SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA	-30	-	-	V	
V <sub>DS</sub> temperature coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = -250 μA	-	-24	-	mV/°C	
V <sub>GS(th)</sub> temperature coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>		-	2.2	-		
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-0.6	-	-1.5	V	
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 12 V	-	-	± 10	μA	
		V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 4.5 V	-	-	± 1		
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V	-	-	-1		
		V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	-	-	-10		
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -3.7 A	-	0.034	0.045	Ω	
		V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -2 A	-	0.041	0.053		
		V <sub>DS</sub> = -2.5 V, I <sub>D</sub> = -2 A	-	0.068	0.081		
Dynamic <sup>b</sup>							
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> = -15 V, V <sub>GS</sub> = -10 V, I <sub>D</sub> = -3.7 A	-	22.8	35	nC	
		V <sub>DS</sub> = -15 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -3.7 A	-	10.6	16		
Gate-source charge	Q <sub>gs</sub>		-	1.7	-		
Gate-drain charge	Q <sub>gd</sub>		-	2.6	-		
Gate resistance	R <sub>g</sub>	f = 1 MHz	2.2	11	22	Ω	
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = -15 V, R <sub>L</sub> = 5.2 Ω, I <sub>D</sub> ≅ -2.9 A, V <sub>GEN</sub> = -4.5 V, R <sub>g</sub> = 1 Ω	-	28	42	ns	
Rise time	t <sub>r</sub>		-	65	98		
Turn-off delay time	t <sub>d(off)</sub>		-	47	71		
Fall time	t <sub>f</sub>		-	62	93		
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = -15 V, R <sub>L</sub> = 5.2 Ω, I <sub>D</sub> ≅ -2.9 A, V <sub>GEN</sub> = -10 V, R <sub>g</sub> = 1 Ω	-	7	14		
Rise time	t <sub>r</sub>		-	8	16		
Turn-off delay time	t <sub>d(off)</sub>		-	52	78		
Fall time	t <sub>f</sub>		-	52	78		
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	-1.4	A	
Pulse diode forward current	I <sub>SM</sub>		-	-	-20		
Body diode voltage	V <sub>SD</sub>	I <sub>S</sub> = -2.9 A, V <sub>GS</sub> = 0 V	-	-0.8	-1.2	V	
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = -2.9 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C	-	13	20	ns	
Body diode reverse recovery charge	Q <sub>rr</sub>		-	6	12	nC	
Reverse recovery fall time	t <sub>a</sub>		-	9	-	ns	
Reverse recovery rise time	t <sub>b</sub>		-	4	-		

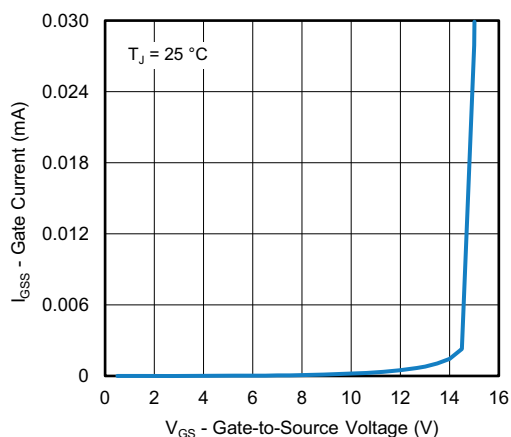
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing

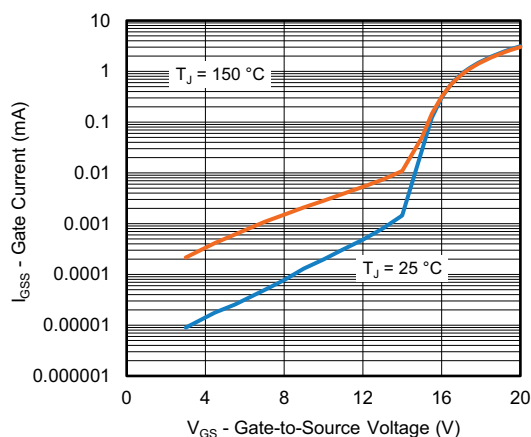
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



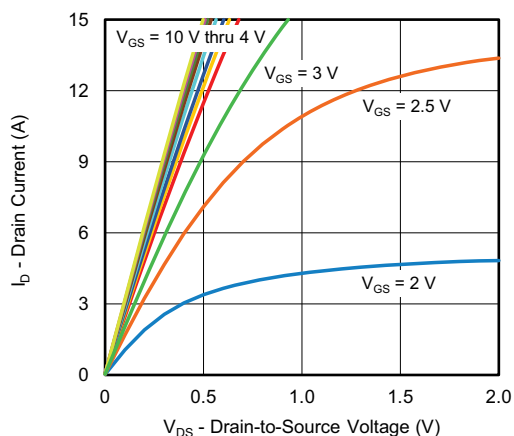
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



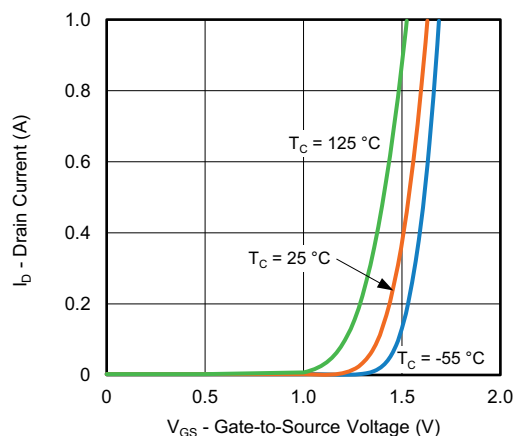
**Gate Current vs. Gate-Source Voltage**



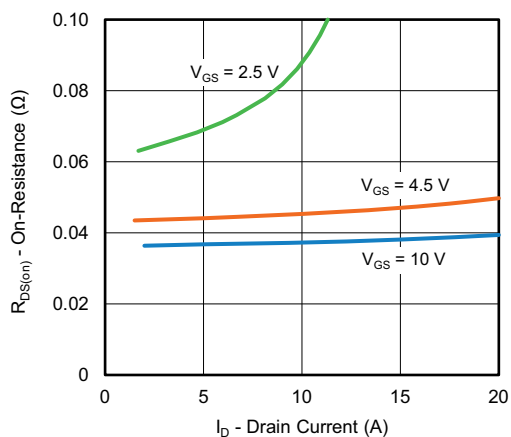
**Gate Current vs. Gate-Source Voltage**



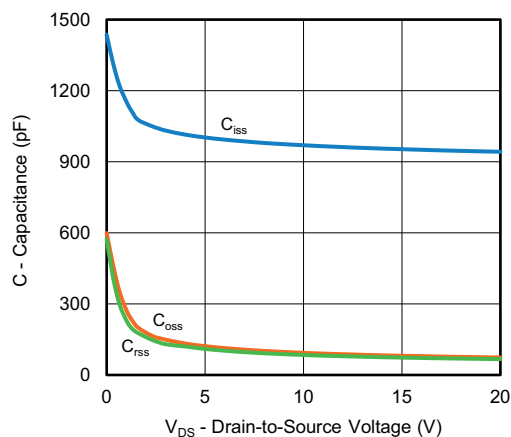
**Output Characteristics**



**Transfer Characteristics**



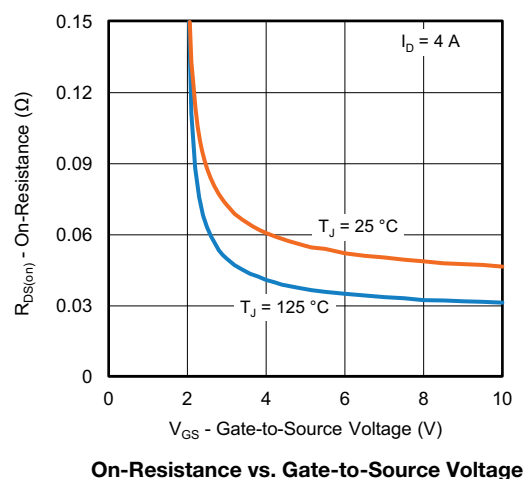
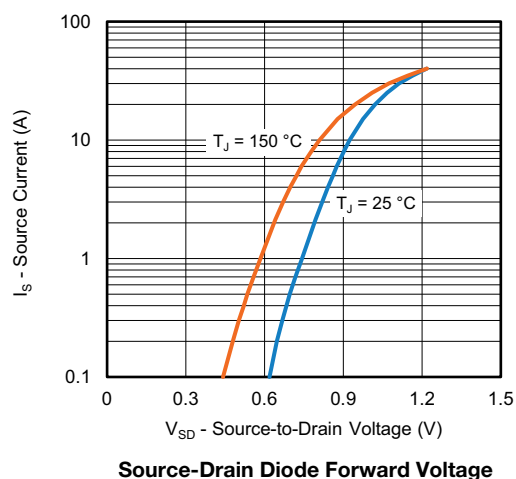
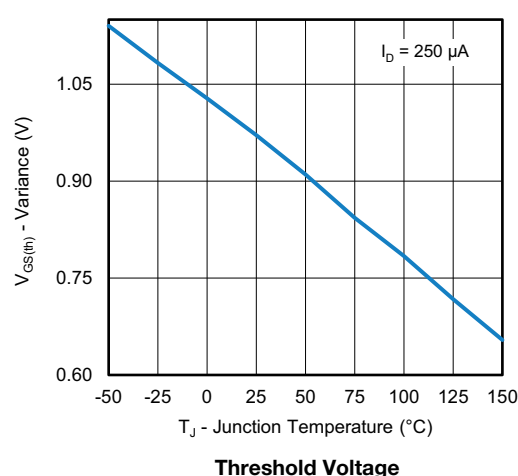
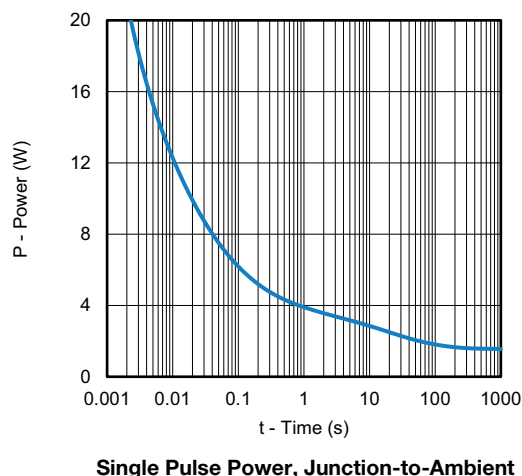
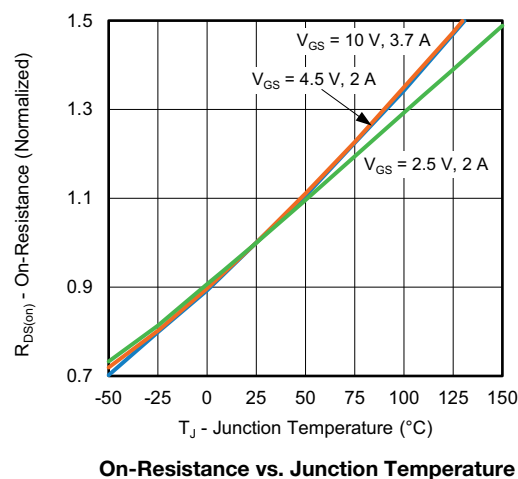
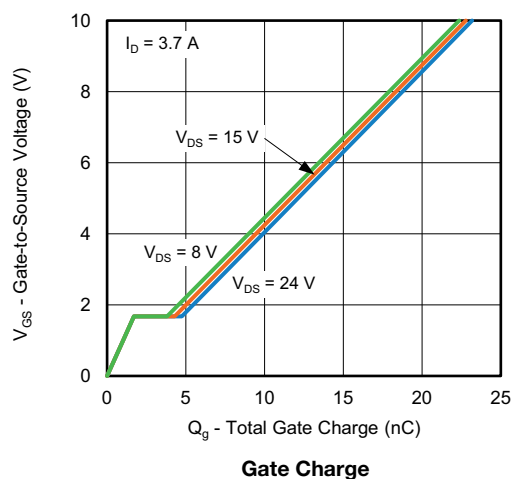
**On-Resistance vs. Drain Current**



**Capacitance**

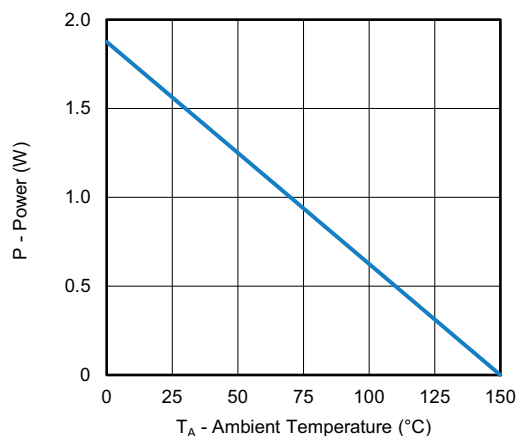
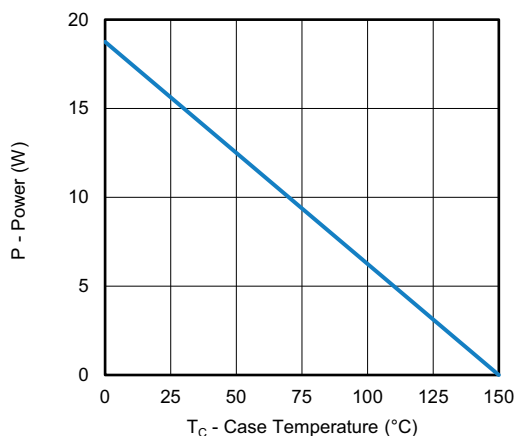
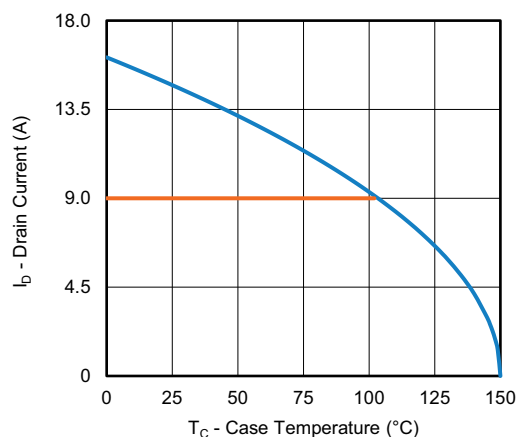
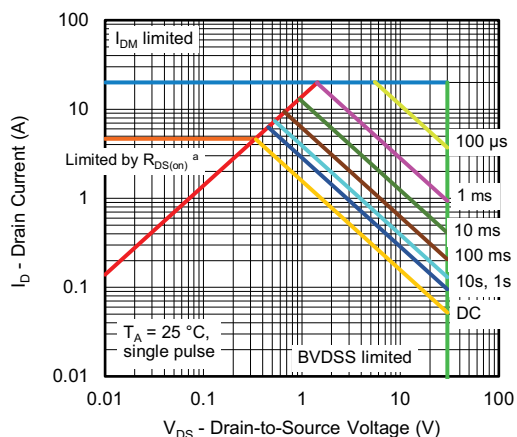


**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)





**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

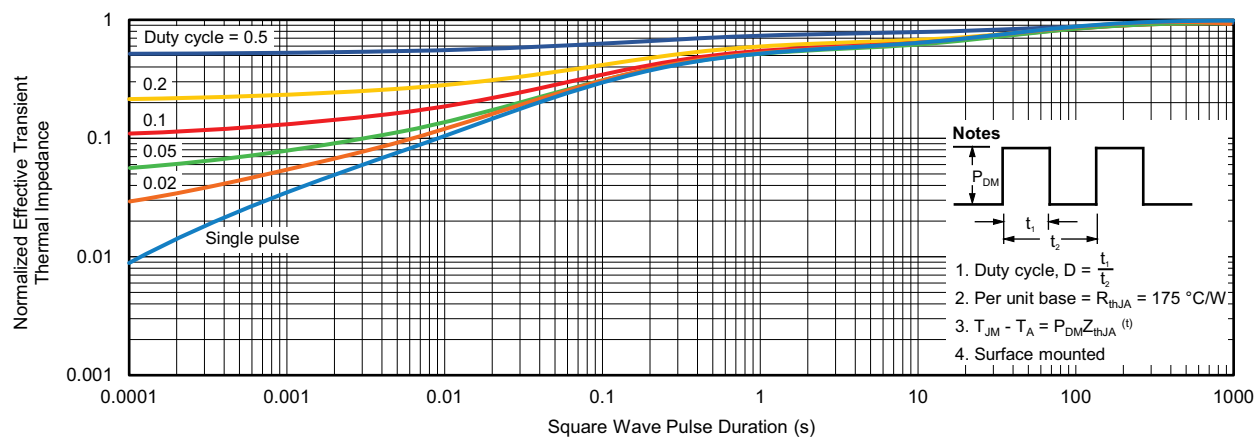


**Note**

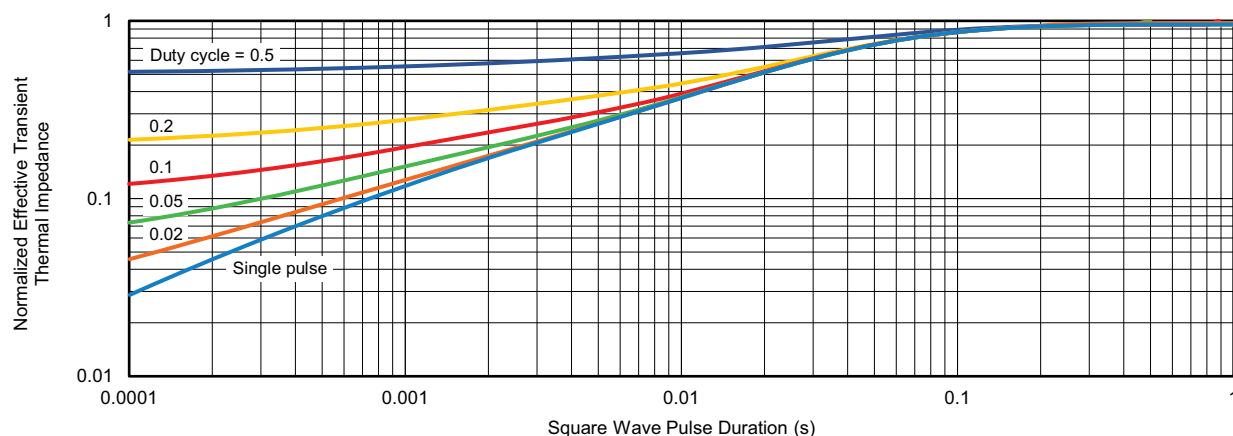
- a. The power dissipation  $P_D$  is based on  $T_J(\text{max.}) = 150\text{ °C}$ , using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Foot**

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